

Data sheet acquired from Harris Semiconductor

SCHS267

January 1997

NOT RECOMMENDED FOR NEW DESIGNS Use CMOS Technology

· Buffered Inputs

Features

- Typical Propagation Delay: 6.8ns at V_{CC} = 5V, $T_A = 25^{\circ}C, C_L = 50pF (FCT843A)$
- CD74FCT843A
 - Noninverting
- CD74FCT844A
 - Inverting
- · SCR Latchup Resistant BiCMOS Process and

CD74FCT843A, CD74FCT844A

BiCMOS FCT Interface Logic, 9-Bit Transparent Latches, Three-State

Circuit Design

- Speed of Bipolar FAST™/AS/S
- 48mA Output Sink Current
- Output Voltage Swing Limited to 3.7V at V_{CC} = 5V
- Controlled Output Edge Rates
- Input/Output Isolation to V_{CC}
- BiCMOS Technology with Low Quiescent Power

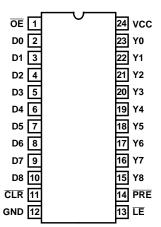
Ordering Information

PART NUMBER	TEMP. RANGE (°C)	PACKAGE	PKG. NO.	
CD74FCT844AEN	0 to 70	24 Ld PDIP	E24.3	
CD74FCT843AM	0 to 70	24 Ld SOIC	M24.3	

NOTE: When ordering the suffix M package, use the entire part number. Add the suffix 96 to obtain the variant in the tape and reel.

Pinouts

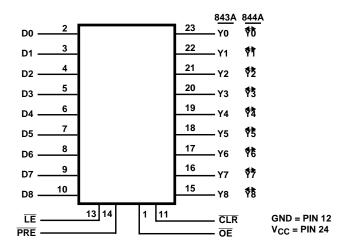
CD74FCT843A (SOIC) TOP VIEW



CD74FCT844A (PDIP) TOP VIEW

ΟE	1	O	24	vcc
D0	2		23	<u>70</u>
D1	3		22	<u>Y1</u>
D2	4		21	<u>72</u>
D3	5		20	<u>73</u>
D4	6		19	<u>74</u>
D5	7		18	<u>Y5</u>
D6			17	<u>Y6</u>
D7	9		16	Y7
D8	10		15	<u>78</u>
CLR	11		14	PRE
GND	12		13	ΙĒ

Functional Diagram



TRUTH TABLE (Note 1)

		OUTPUTS					
CLR	PRE	ŌĒ	ĪĒ.	843A Dn	844A Dn	Yn	FUNCTION
Н	Н	Н	Χ	Χ	Х	Z	High Z
Н	Н	Н	L	Χ	Х	Z	Latched (High Z)
Н	Н	L	Н	L	Н	L	Transparent
Н	Н	L	Н	Н	L	Н	Transparent
Н	Н	L	L	Х	Х	NC	Latched
Н	L	L	Х	Х	Х	Н	Preset
L	Н	L	Х	Х	Х	L	Clear
L	L	L	Х	Х	Х	Н	Preset
L	Н	Н	L	Х	Х	Z	Latched (High Z)
Н	L	Н	L	Х	Х	Z	Latched (High Z)

NOTE:

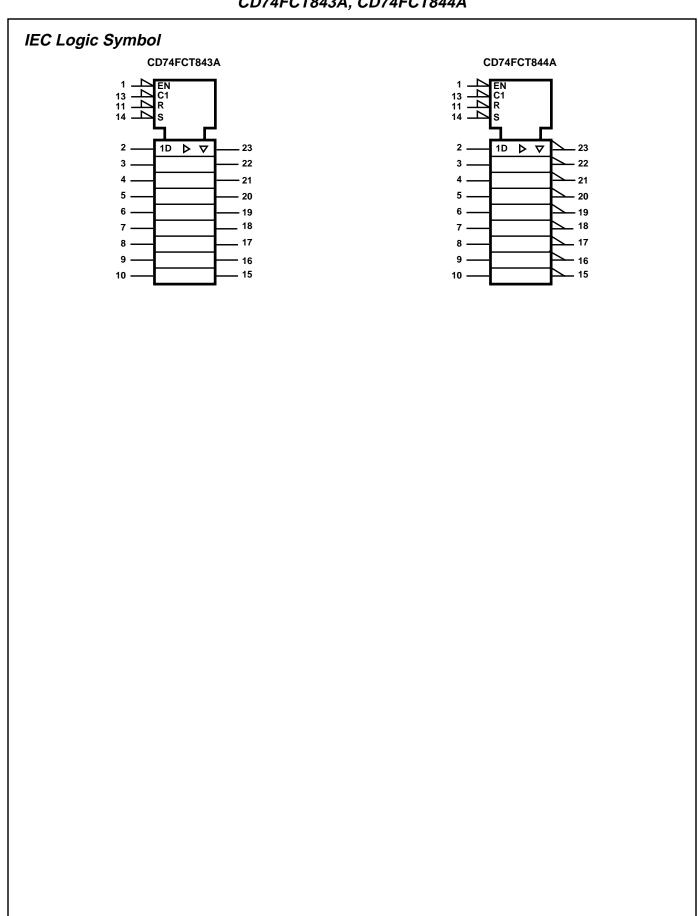
1. H= HIGH Voltage Level

L = LOW Voltage Level

X = Immaterial

NC = No Change

Z = High Impedance



Absolute Maximum Ratings

DC Supply Voltage (V _{CC})	-0.5V to 6V
DC Diode Current, I _{IK} (For V _I < -0.5V)	20mA
DC Output Diode Current, I_{OK} (for $V_O < -0.5V$)	50mA
DC Output Sink Current per Output Pin, IO	70mA
DC Output Source Current per Output Pin, IO	30mA
DC V _{CC} Current (I _{CC})	237mA
DC Ground Current (I _{GND})	453mA

Thermal Information

Thermal Resistance (Typical, Note 2)	θ _{JA} (^o C/W)
PDIP Package	75
SOIC Package	75
Maximum Junction Temperature	150 ^o C
Maximum Storage Temperature Range	65°C to 150°C
Maximum Lead Temperature (Soldering 10s)	300°C
(SOIC-Lead Tips Only)	

Operating Conditions

Operating Temperature Range, T _A	
Supply Voltage Range, VCC	4.75V to 5.25V
DC Input Voltage, V ₁	0 to $V_{\mbox{\footnotesize{CC}}}$
DC Output Voltage, VO	$\dots \dots 0$ to $\leq V_{CC}$
Input Rise and Fall Slew Rate, dt/dv	0 to 10ns/V

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

NOTE

2. θ_{JA} is measured with the component mounted on an evaluation PC board in free air.

Electrical Specifications Commercial Temperature Range 0° C to 70° C, V_{CC} Max = 5.25V, V_{CC} Min = 4.75V

					AMBIENT TEMPERATURE (T _A)						
		TEST CO	TEST CONDITIONS		EST CONDITIONS		25°C		0°C T	O 70°C]
PARAMETER	SYMBOL	V _I (V)	I _O (mA)	V _{CC} (V)	MIN	MAX	MIN	MAX	UNITS		
High Level Input Voltage	V _{IH}			4.75 to 5.25	2	-	2	-	V		
Low Level Input Voltage	V _{IL}			4.75 to 5.25	-	0.8	-	0.8	V		
High Level Output Voltage	V _{OH}	V _{IH} or V _{IL}	-15	Min	2.4	-	2.4	-	V		
Low Level Output Voltage	V _{OL}	V _{IH} or V _{IL}	48	Min	-	0.55	-	0.55	V		
High Level Input Current	l _{IH}	V _{CC}		Max	-	0.1	-	1	μΑ		
Low Level Input Current	I _{IL}	GND		Max	-	-0.1	-	-1	μΑ		
Three-State Leakage Current	lozh	V _{CC}		Max	-	0.5	-	10	μΑ		
	I _{OZL}	GND		Max	-	-0.5	-	-10	μΑ		
Input Clamp Voltage	V _{IK}	V _{CC} or GND	-18	Min	-	-1.2	-	-1.2	V		
Short Circuit Output Current (Note 3)	los	$V_{O} = 0$ V_{CC} or GND		Max	-75	-	-75	-	mA		
Quiescent Supply Current, MSI	Icc	V _{CC} or GND	0	Max	-	8	-	80	μА		
Additional Quiescent Supply Current per Input Pin TTL Inputs High, 1 Unit Load	Δl _{CC}	3.4V (Note 4)		Max	-	1.6	-	1.6	mA		

NOTES:

- 3. Not more than one output should be shorted at one time. Test duration should not exceed 100ms.
- 4. Inputs that are not measured are at VCC or GND.
- 5. FCT Input Loading: All inputs are 1 unit load. Unit load is ΔI_{CC} limit specified in Static Characteristics Chart, e.g., 1.6mA Max. @ $70^{\circ}C$.

Switching Specifications Over Operating Range FCT Series t_r , t_f = 2.5ns, C_L = 50pF, R_L (Figure 1)

				25°C	0°C T	O 70°C	
PARAME [*]	TER	SYMBOL	V _{CC} (V)	TYP	MIN	MAX	UNITS
Propagation Delays							
Data to Outputs	CD74FCT843A	t _{PLH} , t _{PHL}	5 (Note 6)	6.8	1.5	9	ns
	CD74FCT844A	t _{PLH} , t _{PHL}	5	7.5	1.5	10	ns
LE to Outputs		t _{PLH} , t _{PHL}	5	9	1.5	12	ns
PRE to Outputs		t _{PLH}	5	9	1.5	12	ns
CLR to Outputs		t _{PHL}	5	9.8	1.5	13	ns
Output Enable Times		t _{PZL} , t _{PZH}	-	10.5	1.5	14	ns
Output Disable Times		t _{PLZ} , t _{PHZ}	-	6	1.5	8	ns
Power Dissipation Capacitance		C _{PD} (Note 7)	-	-	-	-	pF
Minimum (Valley) V _{OHV} During Swi Other Outputs (Output Under Test N		V _{OHV}	5	0.5	-	-	V
Maximum (Peak) V _{OLP} During Switching of Other Outputs (Output Under Test Not Switching)		V _{OLP}	5	1	-	-	V
Input Capacitance		Cl	-	-	-	10	pF
Three-State Output Capacitance		co	-	-	-	15	pF

NOTES:

- 6. 5V: Minimum is at 5.25V for 0°C to 70°C, Maximum is at 4.75V for 0°C to 70°C, Typical is at 5V.
- 7. C_{PD} , measured per flip-flop, is used to determine the dynamic power consumption. P_D (per package) = $V_{CC} I_{CC} + \Sigma (V_{CC}^2 f_I C_{PD} + V_O^2 f_O C_L + V_{CC} \Delta I_{CC} D)$ where:

 V_{CC} = supply voltage

 ΔI_{CC} = flow through current x unit load

C_L = output load capacitance

D = duty cycle of input high

f_O = output frequency

f_I = input frequency

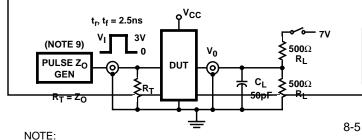
Prerequisite for Switching

			25°C	0°C T	O 70°C	
PARAMETER	SYMBOL	V _{CC} (V)	TYP	MIN	MAX	UNITS
Setup Time, Data to LE	t _{SU}	5 (Note 8)	-	2.5	-	ns
Hold Time, Data to LE	t _H	5	-	2.5	-	ns
LE Pulse Width	t _W	5	-	4	-	ns
PRE, CLR Pulse Width	t _W	5	-	8	-	ns
PRE, CLR Recovery Time	t _{REC}	5	-	14	-	ns

NOTE:

8. Minimum is at 4.75V for 0°C to 70°C, Typical is at 5V.

Test Circuits and Waveforms



SWITCH POSITION

TEST	SWITCH
t _{PLZ} , t _{PZL} , Open Drain	Closed
t _{PHZ} , t _{PZH} , t _{PLH} , t _{PHL}	Open

DEFINITIONS

C_L = Load capacitance, includes jig and probe capacitance.

 R_T = Termination resistance, should be equal to Z_{OUT} of the Pulse Generator.

9. Pulse Generator for All Pulses: Rate $\leq 1.0 \text{MHz}$; $Z_{OUT} \leq 50 \Omega$;

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